MOSFETs Silicon N-Channel MOS (π-MOSVII)

TK3P50D

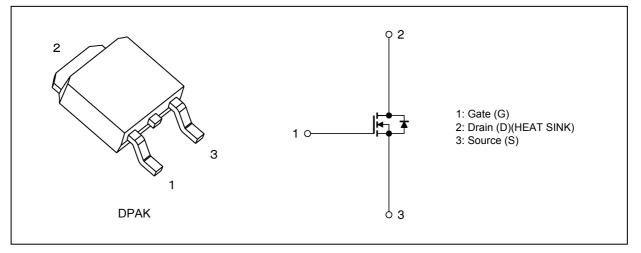
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 2.3 \Omega$ (typ.)
- (2) High forward transfer admittance: $|Y_{fs}| = 1.0 \text{ S}$ (typ.)
- (3) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 500 \ V)$
- (4) Enhancement mode: V_{th} = 2.4 to 4.4 V (V_{DS} = 10 V, I_D = 1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	500	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	Ι _D	3	A
Drain current (pulsed)	(Note 1)	I _{DP}	6	
Power dissipation (T _c = 25°C	;)	PD	60	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	81	mJ
Avalanche current		I _{AR}	3	Α
Repetitive avalanche energy	(Note 3)	E _{AR}	6	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	2.08	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	125	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 15.3 mH, R_G = 25 Ω , I_{AR} = 3 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

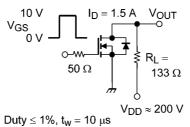
6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	500	_	_	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.4	—	4.4	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 1.5 A	_	2.3	3.0	Ω
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 1.5 A	0.3	1		S

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	280	_	pF
Reverse transfer capacitance	C _{rss}		_	1.5	_	
Output capacitance	C _{oss}			30	_	
Switching time (rise time)	t _r	See Figure 6.2.1.		20	_	ns
Switching time (turn-on time)	t _{on}		_	50	_	
Switching time (fall time)	t _f			10	_	
Switching time (turn-off time)	t _{off}		_	80	_	



Duty $\leq 1\%$, $t_W = 10 \ \mu s$

Fig. 6.2.1 Switching Time Test Circuit

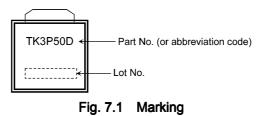
6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} \text{ = } 10 \text{V}, \text{I}_{D} \text{ = } 3 \text{A}$	_	7	—	nC
Gate-source charge	Q _{gs}		_	4	_	
Gate-drain charge	Q _{gd}		_	3	_	

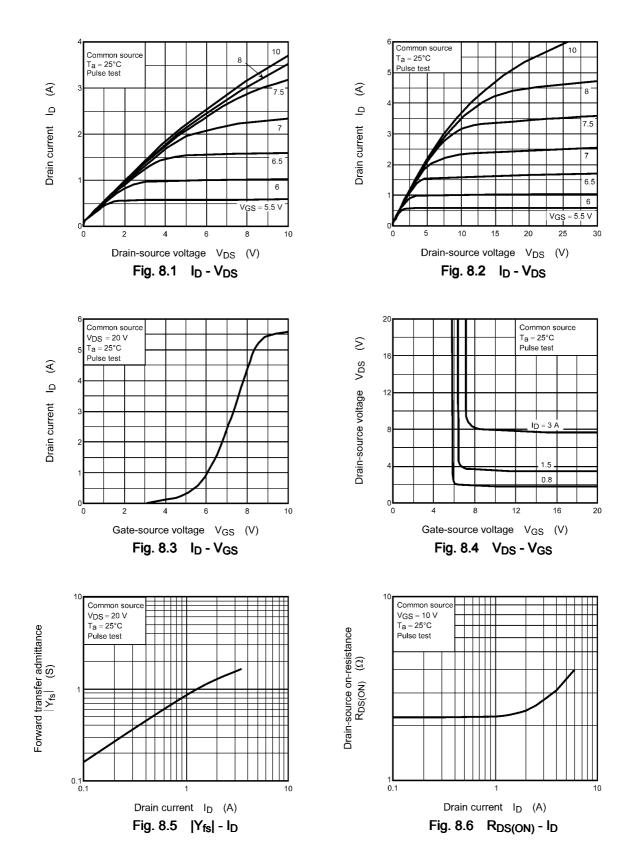
6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

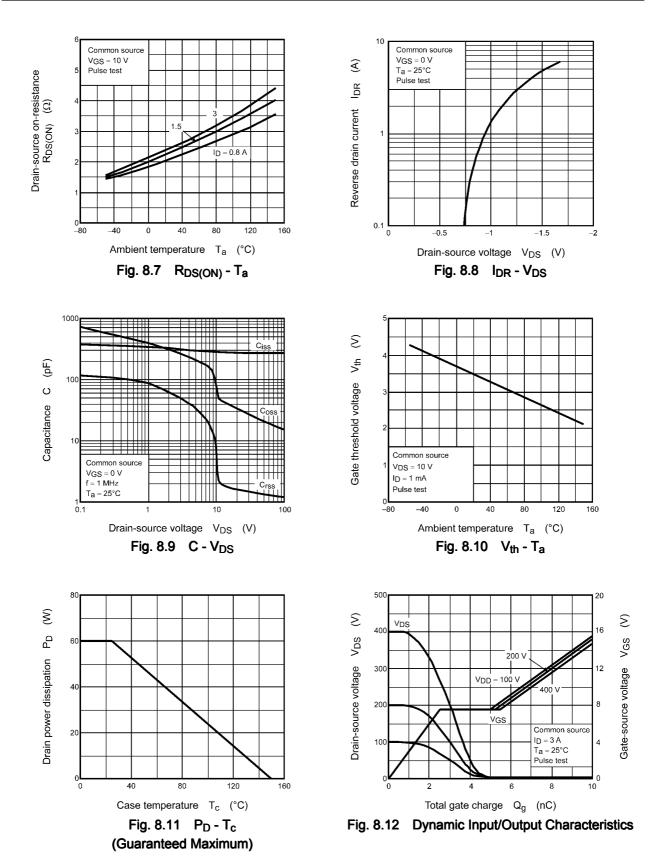
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 1)	I _{DR}	—	_	_	3	А
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	—	_	_	6	
Diode forward voltage		V _{DSF}	I _{DR1} = 3 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time		t _{rr}	I _{DR} = 3 A, V _{GS} = 0 V	_	770	_	ns
Reverse recovery charge		Q _{rr}	-dI _{DR} /dt = 100 A/μs		2.5	_	μC

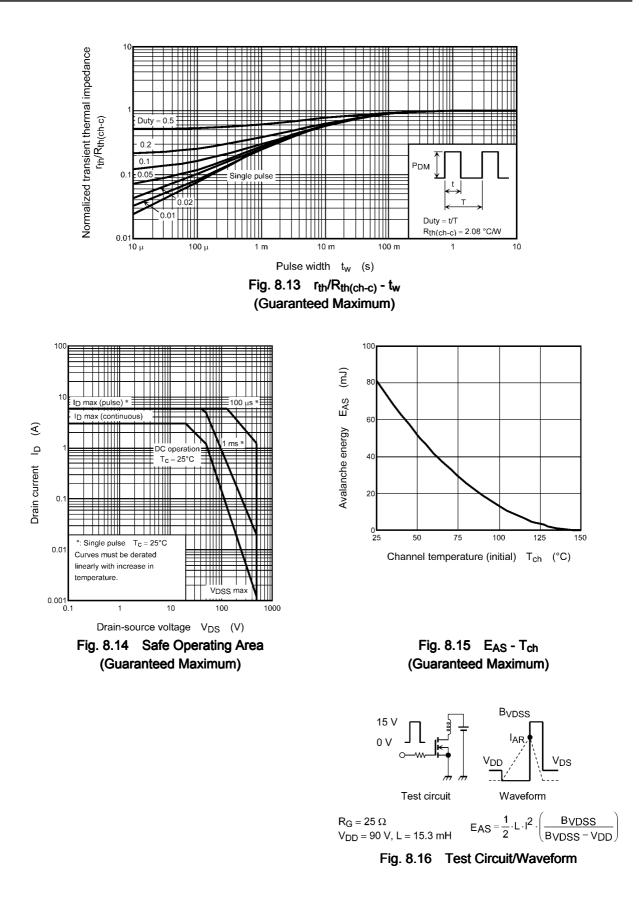
7. Marking



8. Characteristics Curves (Note)





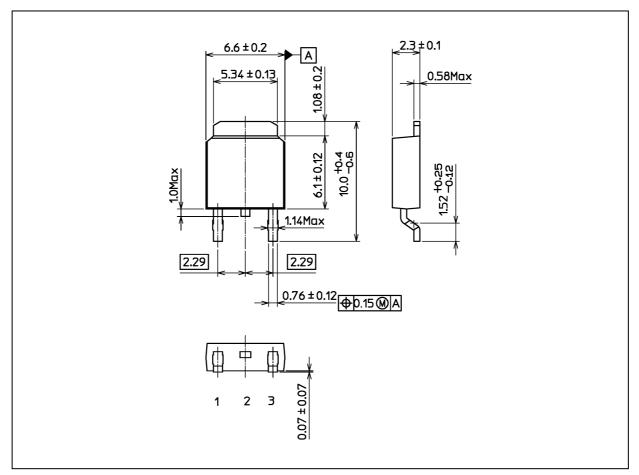


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

Package Name(s)
TOSHIBA: 2-7K1S
Nickname: DPAK

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